

PSMN3R4-30PL

N-channel 30 V 3.4 mΩ logic level MOSFET

Rev. 01 — 2 November 2010

Product data sheet

1. Product profile

1.1 General description

Logic level N-channel MOSFET in TO220 package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for logic level gate drive sources

1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$		-	-	30	V
I _D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u>	[1]	-	-	100	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	114	W
Tj	junction temperature			-55	-	175	°C
Static character	ristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 10 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 13}{}$		-	3.5	4.1	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 13}{}$	[2]	-	2.8	3.4	mΩ
Dynamic chara	cteristics						
Q_{GD}	gate-drain charge	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A};$		-	8	-	nC
Q _{G(tot)}	total gate charge	V _{DS} = 15 V; see <u>Figure 14</u> ; see <u>Figure 15</u>		-	31	-	nC
Avalanche ruggedness							
E _{DS(AL)} S	non-repetitive drain-source avalanche energy	$\begin{split} &V_{GS} = 10 \text{ V; } T_{j(init)} = 25 \text{ °C;} \\ &I_D = 100 \text{ A; } V_{sup} \leq 30 \text{ V;} \\ &R_{GS} = 50 \text{ \Omega; unclamped} \end{split}$		-	-	200	mJ



- [1] Continuous current is limited by package.
- [2] Measured 3 mm from package.

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain	mb	D
3	S	source		
mb	D	mounting base; connected to drain	1 2 3	mbb076 S
			SOT78 (TO-220AB)	

3. Ordering information

Table 3. Ordering information

Type number Package			
	Name	Description	Version
PSMN3R4-30PL	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		0 11:1				
Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	30	V
V_{DGR}	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$		-	30	V
V_{GS}	gate-source voltage			-20	20	V
I _D	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 100 ^{\circ}\text{C}; \text{see } \frac{\text{Figure 1}}{\text{M}}$	[1]	-	100	Α
		$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$	[1]	-	100	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 \text{ °C}$; see Figure 3		-	609	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	114	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drai	in diode					
Is	source current	T _{mb} = 25 °C	[1]	-	100	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	609	Α
Avalanche i	ruggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 100 A; $V_{sup} \le$ 30 V; R_{GS} = 50 Ω ; unclamped		-	200	mJ

[1] Continuous current is limited by package.

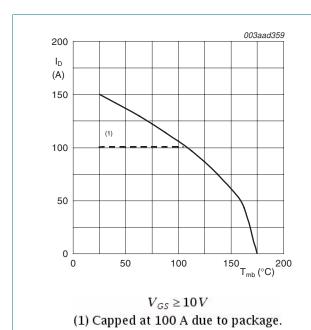


Fig 1. Continuous drain current as a function of mounting base temperature

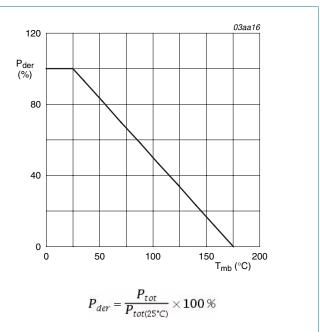
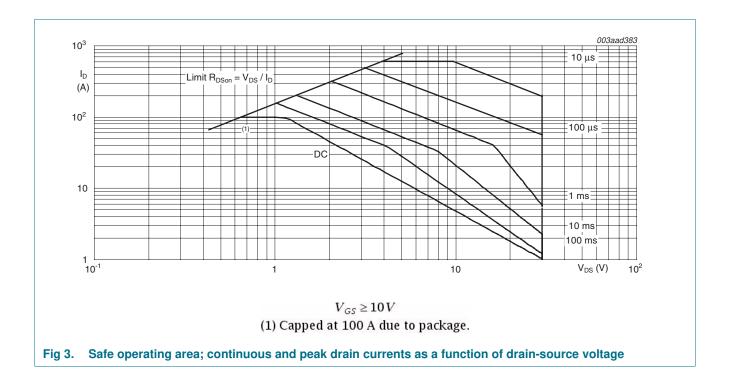


Fig 2. Normalized total power dissipation as a function of mounting base temperature



5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	0.65	1	K/W

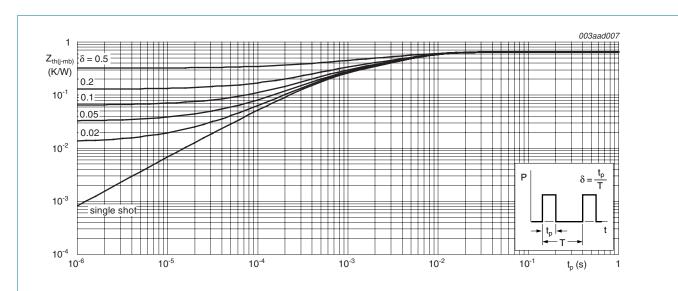


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration; typical values

6. Characteristics

Table 6. Characteristics

Tested to JEDEC standards where applicable.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics					
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	30	-	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	27	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 25$ °C; see <u>Figure 10</u> ; see <u>Figure 11</u>	1.3	1.7	2.15	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 175$ °C; see Figure 11	0.5	-	-	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = -55$ °C; see Figure 11	-	-	2.45	V
I _{DSS}	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.3	5	μΑ
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ °C}$	-	-	100	μΑ
I_{GSS}	gate leakage current	$V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
		V_{GS} = -16 V; V_{DS} = 0 V; T_j = 25 °C	-	10	100	nA
R _{DSon} drain-source on-state resistanc	V_{GS} = 10 V; I_D = 10 A; T_j = 175 °C; see <u>Figure 12</u>	-	-	6.46	mΩ	
		V_{GS} = 4.5 V; I_D = 10 A; T_j = 25 °C; see Figure 13	-	3.5	4.1	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 100 \text{ °C};$ see Figure 12	-	-	6.1	mΩ
	$V_{GS} = 4.5 \text{ V}; I_D = 10 \text{ A}; T_j = 175 \text{ °C};$ see <u>Figure 12</u>	-	-	7.79	mΩ	
		$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 25 \text{ °C};$ see Figure 13	[1] -	2.8	3.4	mΩ
R_{G}	gate resistance	f = 1 MHz	-	1	-	Ω
Dynamic ch	aracteristics					
Q _{G(tot)}	total gate charge	$I_D = 25 \text{ A}$; $V_{DS} = 15 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 14; see Figure 15	-	64	-	nC
		$I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V$	-	58	-	nC
		$I_D = 25 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$	-	31	-	nC
Q _{GS}	gate-source charge	see <u>Figure 14</u> ; see <u>Figure 15</u>	-	12	-	nC
Q _{GS(th)}	pre-threshold gate-source charge		-	6.2	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	5.8	-	nC
Q _{GD}	gate-drain charge		-	8	-	nC
V _{GS(pl)}	gate-source plateau voltage	V _{DS} = 15 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	2.8	-	V
C _{iss}	input capacitance	$V_{DS} = 12 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	3907	-	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 16</u>	-	822	-	pF
C _{rss}	reverse transfer capacitance		-	356	-	pF

 Table 6.
 Characteristics ...continued

Tested to JEDEC standards where applicable.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$t_{d(on)}$	turn-on delay time	V_{DS} = 12 V; R_{L} = 0.5 Ω ; V_{GS} = 4.5 V; $R_{G(ext)}$ = 4.7 Ω	-	40	-	ns
t _r	rise time		-	73	-	ns
t _{d(off)}	turn-off delay time		-	59	-	ns
tf	fall time		-	28	-	ns
Source-dra	in diode					
V_{SD}	source-drain voltage	$I_S = 10 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 17</u>	-	0.7	1.2	V
t _{rr}	reverse recovery time	$I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$ $V_{GS} = 0 \text{ V}; V_{DS} = 12 \text{ V}$	-	36	-	ns
Q _r	recovered charge		-	28	-	nC

[1] Measured 3 mm from package.

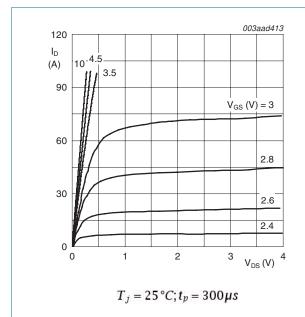


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

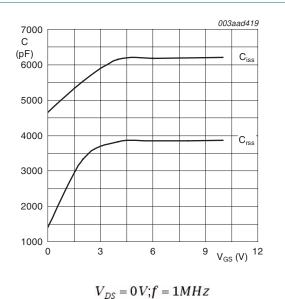


Fig 6. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

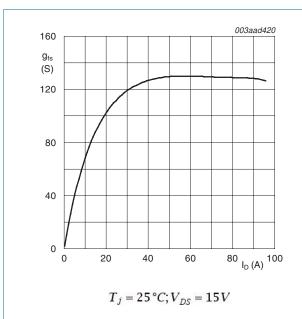


Fig 7. Forward transconductance as a function of drain current; typical values

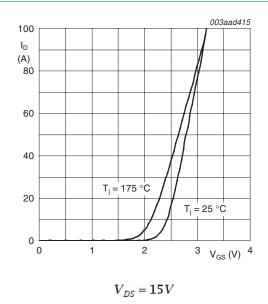
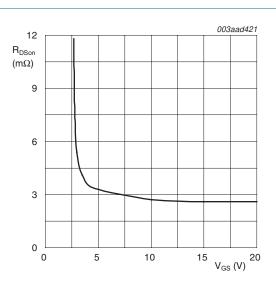
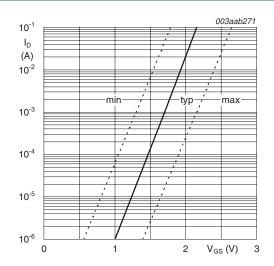


Fig 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values



 $T_j=25\,^{\circ}C; I_D=25A$

Fig 8. Drain-source on-state resistance as a function of gate-source voltage; typical values



$$T_j = 25 \,^{\circ}C; V_{DS} = 5V$$

Fig 10. Sub-threshold drain current as a function of gate-source voltage

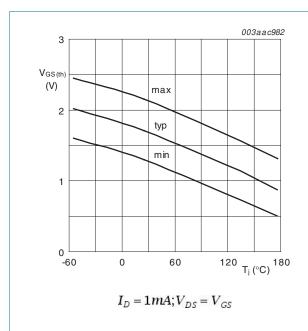
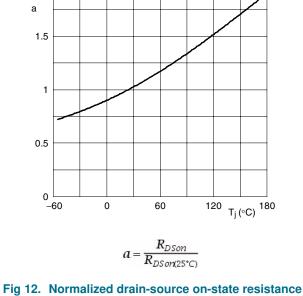


Fig 11. Gate-source threshold voltage as a function of junction temperature



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Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature

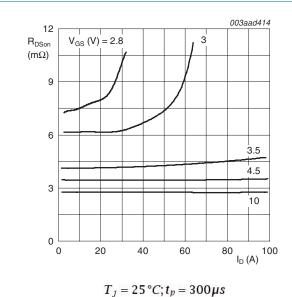


Fig 13. Drain-source on-state resistance as a function of drain current; typical values

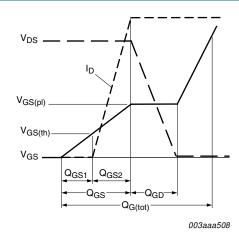


Fig 14. Gate charge waveform definitions

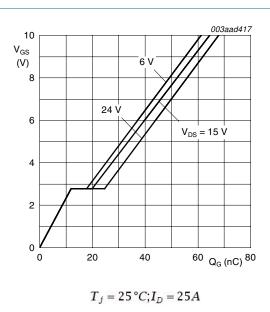
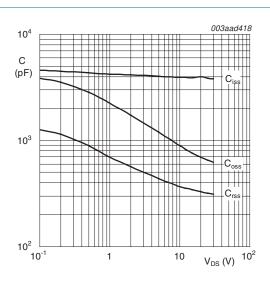


Fig 15. Gate-source voltage as a function of gate charge; typical values



 $V_{GS} = 0V; f = 1MHz$

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

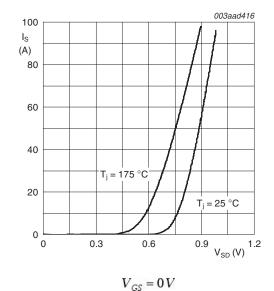
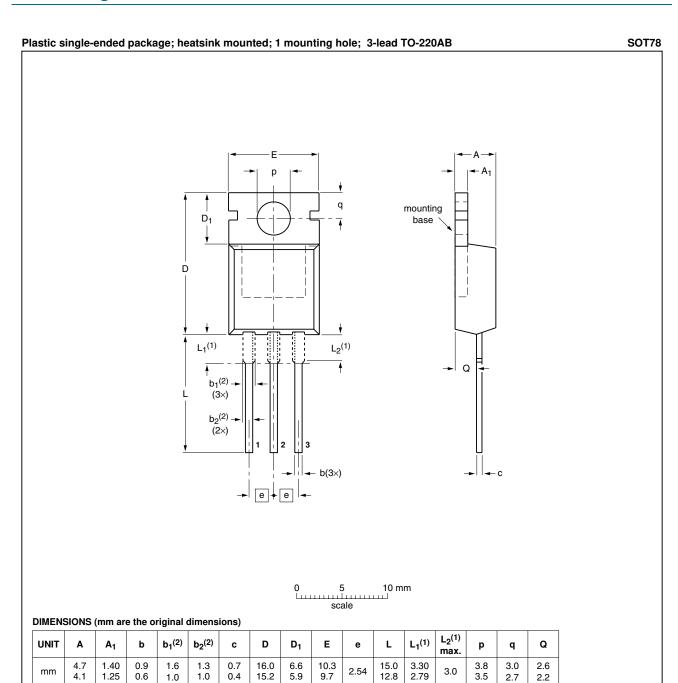


Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

7. Package outline



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- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE	
SOT78		3-lead TO-220AB	SC-46		08-04-23 08-06-13	

Fig 18. Package outline SOT78 (TO-220AB)

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8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN3R4-30PL v.1	20101102	Product data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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